- 16. (New) The method of claim 5, wherein the semiconductor layer is formed by supplying a material gas heated to a temperature of 1020°C.
- 17. (New) The method of claim 7, wherein the semiconductor layer is formed by supplying a material gas heated to a temperature of 1020°C.

## **REMARKS**

In the preliminary amendment, Applicants have submitted new claims 14-17 for consideration. Applicants submit that new claims 14-17 are in condition for allowance, an indication for which is respectfully solicited. No new matter has been added.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

Michael E. Fogarty

Registration No. 36,139

600 13<sup>th</sup> Street, N.W. Washington, DC 20005-3096 (202) 756-8000 MEF:men Facsimile: (202) 756-8087

Date: June 20, 2003